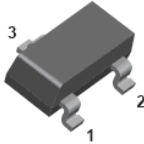


KTC3880S

NPN Silicon Epitaxial Planar Transistor

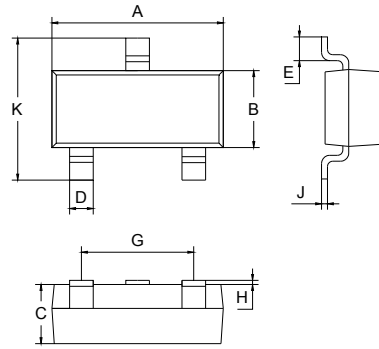


FEATURES

- Small reverse transfer capacitance.
- Low noise figure.

APPLICATIONS

- High frequency Low noise amplifier application.
- VHF band amplifier application.



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.1 Typical	
K	2.20	2.60
All Dimensions in mm		

ORDERING INFORMATION

Type No.	Marking	Package Code
KTC3880S	AQR/AQO/AQY	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current	20	mA
I_E	Emitter Current	-20	mA
P_C	Collector Power Dissipation	150	mW
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

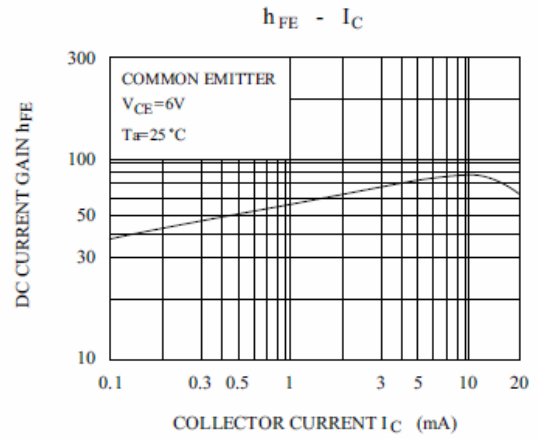
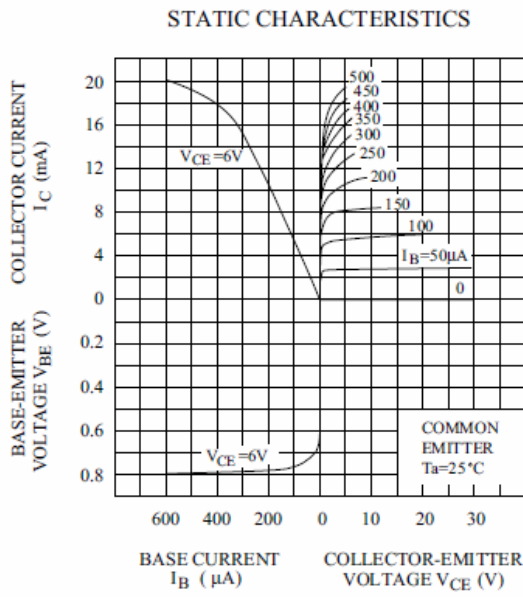
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	$V_{CB}=18V, I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=1mA$	40		200	
Transition frequency	f_T	$V_{CE}=6V, I_C=1mA$	300	550		MHz
Reverse Transfer Capacitance	C_{re}	$V_{CB}=6V, I_E=0, f=1MHz$		0.7		pF
Collector-Base Time Constant	C_{c-rbb}	$V_{CB}=6V, I_E=-1mA$ $f=30MHz$			30	pS
Noise figure	NF	$V_{CC}=6V, I_E=-1mA,$ $f=100KHz$		2.5	5.0	dB
Power Gain	G_{pe}		15	18		

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	100-200
Marking	AQR	AQO	AQY



TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



Device	Package	Shipping
KTC3880S	SOT-23	3000/Tape&Reel